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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | Complete if Known | | | |
| | | Application Number | 10/610,481 | | |
| | | Filing Date | June 30, 2003 | | |
| | | First Named Inventor | Tuschel, David | | |
| | | Group Art Unit | 2877 | | |
| | | Examiner Name | [Not Assigned] | | |
| Sheet | 2 | 030 | 3 | Attorney Docket Number | 030354 |

| OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS | | | |
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| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
| SL | BA | MIZOGUCHI et al. "Raman image study of flash-lamp annealing of ion-implanted silicon" <i>Journal of Applied Physics</i> 77 (7) 1 April 1995, pp. 3388-3392. | |
| SL | BB | OTHONOS et al., "Raman spectroscopy and spreading resistance analysis of phosphorous implanted and annealed silicon", <i>Journal of Applied Physics</i> 75 (12) 15 June 1994, pp. 8032-8038. | |
| SL | BC | OTHONOS et al., "Multi-wavelength Raman probing of phosphorus implanted silicon wafers", <i>Nucl. Instr. and Meth. in Phys. Rev. B</i> 117 (1996) pp. 367-374 | |
| SL | BD | CHRISTOFIDES et al., "Reconstruction mechanisms in ion implanted and annealed silicon wafers", <i>Defect and Diffusion Forum</i> Vols. 117-118 (1985), pp. 45-64 | |
| SL | BE | ISHIOKA et al. "Reduction in Raman Intensity of Si (1 1 1) Due to Defect Formation During Ion Irradiation", <i>Solid State Communications</i> , Vol. 96, No. 6, pp. 387-390 (1995). | |
| SL | BF | DEY et al, "Raman scattering characterization of Si(100) implanted with mega-electron-volt Sb", <i>Journal of Applied Physics</i> 87 (3) 1 February 2000, pp. 1110-1116 | |
| SL | BG | JAIN et al, "Raman scattering from ion-implanted silicon" <i>Physical Review B</i> . Vol. 32, No. 10, 15 November 1985, pp. 6688-6691 | |
| SL | BH | DEWILTON et al, "RAMAN SPECTROSCOPY FOR NONDESTRUCTIVE DEPTH PROFILE STUDIES OF ION IMPLANTATION IN SILICON", <i>J. Electrochem. Soc.: SOLID STATE SCIENCE AND TECHNOLOGY</i> , May 1986, pp. 988-993 | |
| SL | BI | ZHANG et al "Details of the Damage Profile in Self-Ion-Implanted Silicon", vol. 25 <i>Journal of Raman Spectroscopy</i> , pp. 515-520 (1994). | |
| SL | BJ | GORELICK, "Raman And Non-Linear Light Scattering From Undersurface Layers Of Ion Implanted Silicon Crystals", <i>materials Science Forum</i> , vol. 173-174 (1995) pp. 237-242 | |
| SL | BK | NAKASHIMA et al. "Raman microprobe study of recrystallization in ion-implanted and laser-annealed polycrystalline silicon" <i>Journal of Applied Physics</i> 54 (5) May. 1983, pp. 2611-2617 | |

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| Examiner Signature | | Date Considered | 11/14/03 |
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| | BL | SHUKLA et al, "Raman scattering from ultraheavily-ion-implanted and laser-annealed silicon" <i>Physical Review B</i> . Vol. 34, No. 12, 15 December 1986, pp. 8950-8953 | |
| | BM | DEWILTON et al, "A Raman study of the dopant distribution in submicron pn junctions in B ⁺ or BF ₂ ⁺ ion implanted silicon", <i>SPIE Vol. 623 Advanced Processing and Characterization of Semiconductors III</i> 1986, pp.26-34 | |
| | | KIRILOV et al; "Amorphous phase transformation during rapid thermal annealing of ion-implanted Si", <i>Mat'l. Res. Soc. Symp. Proc.</i> , Vol. 52 (1986), pp. 131-138 | |
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